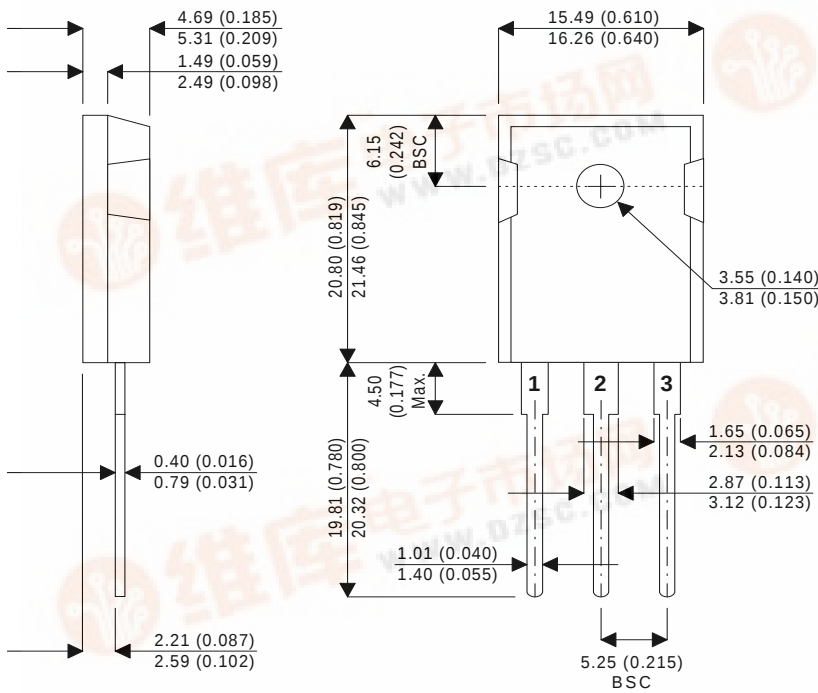


BUZ907P
BUZ908P

MECHANICAL DATA

Dimensions in mm



TO-247

Pin 1 – Gate

Pin 2 – Source
Case – Source

Pin 3 – Drain

P-CHANNEL POWER MOSFET

POWER MOSFETS FOR AUDIO APPLICATIONS

FEATURES

- HIGH SPEED SWITCHING
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (220V & 250V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODES
- COMPLIMENTARY N-CHANNEL
BUZ902P & BUZ903P

ABSOLUTE MAXIMUM RATINGS

($T_{case} = 25^{\circ}C$ unless otherwise stated)

		BUZ907P	BUZ908P
V_{DSX}	Drain – Source Voltage	-220V	-250V
V_{GSS}	Gate – Source Voltage	$\pm 14V$	
I_D	Continuous Drain Current	-8A	
$I_{D(PK)}$	Body Drain Diode	-8A	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	125W	
T_{stg}	Storage Temperature Range	-55 to $150^{\circ}C$	
T_j	Maximum Operating Junction Temperature	$150^{\circ}C$	
$R_{\theta JC}$	Thermal Resistance Junction – Case	$1^{\circ}C/W$	

STATIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSX} Drain – Source Breakdown Voltage	V _{GS} = 10V	BUZ907P	-220		V
	I _D = -10mA	BUZ908P	-250		V
BV _{GSS} Gate – Source Breakdown Voltage	V _{DS} = 0	I _G = ±100μA	±14		V
V _{GS(OFF)} Gate – Source Cut-Off Voltage	V _{DS} = -10V	I _D = -100mA	-0.15	-1.5	V
V _{DS(SAT)} * Drain – Source Saturation Voltage	V _{GD} = 0	I _D = -8A		-12	V
R _{DS(on)} * Static – Source Resistance	V _{GS} = -10	I _D = -8A		1.5	Ω
I _{DSX} Drain – Source Cut-Off Current	V _{GS} = 10V	V _{DS} = -220V BUZ907P		-10	mA
		V _{DS} = -250V BUZ908P		-10	mA
y _{fs} * Forward Transfer Admittance	V _{DS} = -10V	I _D = -3A	0.7	2	S

DYNAMIC CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C _{iss} Input Capacitance	V _{DS} = -10V f = 1MHz		TBA		pF
C _{oss} Output Capacitance			TBA		
C _{rss} Reverse Transfer Capacitance			TBA		
t _{on} Turn-on Time	V _{DS} = -20V		TBA		ns
t _{off} Turn-off Time	I _D = -5A		TBA		

* Pulse Test: Pulse Width = 300μs , Duty Cycle ≤ 2%.

